



Features

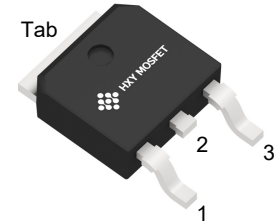
- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low $R_{DS(on)}$
- Easy to drive and parallel
- Effectively lower down T_j and R_{th} , High anti-EMI ability
- RoHS Compliant

Benefits

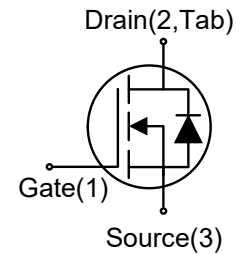
- Increased Power Density
- Faster Operating Frequency
- Reduction of Heat Sink Requirements
- Higher Efficiency
- Reduced EMI

Applications

- Power Factor Correction Modules
- Switch Mode Power Supplies
- Power Inverters
- High Voltage DC/DC Converters



TO-252-2L



Ordering Part Number	Package	Brand
SIHD240N65E-GE3	TO-252-2L	HXY MOSFET

Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions
V_{DSmax}	Drain - Source Voltage	650	V	
V_{GSmax}	Gate - Source Voltage (dynamic)	-5/+26	V	
V_{GSop}	Gate - Source Voltage (static)	0/+15	V	
I_D	Continuous Drain Current	20	A	$T_C = 25^\circ\text{C}$
		17.5		$T_C = 100^\circ\text{C}$
$I_{D(pulse)}$	Pulsed Drain Current	30	A	Pulse width t_p limited by T_{jmax}
P_D	Power Dissipation	52	W	$T_C = 25^\circ\text{C}$
		25		$T_C = 100^\circ\text{C}$
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$	



Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless other wise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	650		850	V	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	
I_{DSS}	Zero Gate Voltage Drain Current		2	100	μA	$V_{GS} = 0\text{ V}$, $V_{DS} = 750\text{ V}$	
I_{GSS+}	Gate-Source Leakage Current			200	nA	$V_{DS} = 0\text{ V}$, $V_{GS} = +22\text{ V}$	
I_{GSS-}	Gate-Source Leakage Current			200	nA	$V_{DS} = 0\text{ V}$, $V_{GS} = -10\text{ V}$	
$V_{GS(th)}$	Gate Threshold Voltage	2.2	3.5	4.2	V	$V_{GS} = V_{DS}$, $I_{DS} = 1\text{ mA}$, $T_J = 25^\circ\text{C}$	Fig. 14
			2.6			$V_{GS} = V_{DS}$, $I_{DS} = 1\text{ mA}$, $T_J = 175^\circ\text{C}$	
$R_{DS(on)}$	Static Drain-Source On-Resistance		160	180	$\text{m}\Omega$	$V_{GS} = 15\text{ V}$, $I_D = 6\text{ A}$, $T_J = 25^\circ\text{C}$	Fig. 15
			195			$V_{GS} = 15\text{ V}$, $I_D = 6\text{ A}$, $T_J = 175^\circ\text{C}$	
C_{iss}	Input Capacitance		208		pF	$V_{DS} = 400\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	Fig. 8
C_{oss}	Output Capacitance		18				
C_{rss}	Reverse Transfer Capacitance		1.8				
Q_g	Total Gate Charge		10.6		nC	$V_{DD} = 400\text{ V}$, $V_{GS} = -5/18\text{ V}$, $I_D = 5\text{ A}$	Fig. 7
Q_{gs}	Gate-Source Charge		5.1				
Q_{gd}	Gate-Drain Charge		2.2				
$R_{G(int)}$	Gate Input Resistance		1.2		Ω	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	
E_{on}	Turn-On Switching Energy		25		μJ	$V_{DD} = 400\text{ V}$, $I_D = 5\text{ A}$, $R_G = 10\ \Omega$, $V_{GS} = -5/18\text{ V}$	Fig. 12
E_{off}	Turn-Off Switching Energy		10				
$t_{d(on)}$	Turn-On Delay Time		5		ns	$V_{DD} = 400\text{ V}$, $I_D = 5\text{ A}$, $R_G = 10\ \Omega$, $V_{GS} = -5/18\text{ V}$	
t_r	Rise Time		17				
$t_{d(off)}$	Turn-Off Delay Time		8				
t_f	Fall Time		10				



Reverse SiC Diode Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	4.0		V	$V_{GS} = -4V, I_{SD} = 5A, T_J = 25^{\circ}C$	Fig. 16
		3.6			$V_{GS} = -4V, I_{SD} = 5A, T_J = 175^{\circ}C$	Fig. 17
$*I_{SD}$	Continuous Diode Forward Current		18	A	$T_C = 25^{\circ}C$	
			10		$T_C = 175^{\circ}C$	
t_{rr}	Reverse Recovery Time	50		ns	$I_{SD} = 5A, di/dt = 1000A/\mu s,$ $V_{DD} = 400V, V_{GS} = -5V$	
Q_{rr}	Reverse Recovery Charge	38		nC		
I_{RRM}	Peak Reverse Recovery Current	2.4		A		

* Depends on bonding wire

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Test Conditions	Note
R_{thJC}	Thermal Resistance from Junction to Case	2.88	$^{\circ}C/W$		Fig. 2
R_{thJA}	Thermal Resistance From Junction to Ambient	40			



Typical Performance

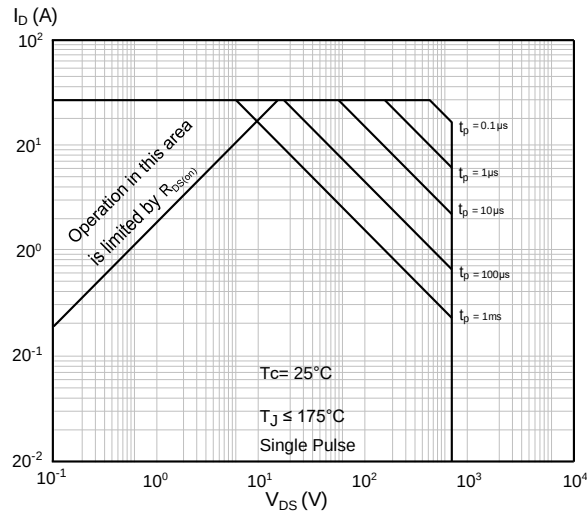


Figure 1. Safe Operating Area

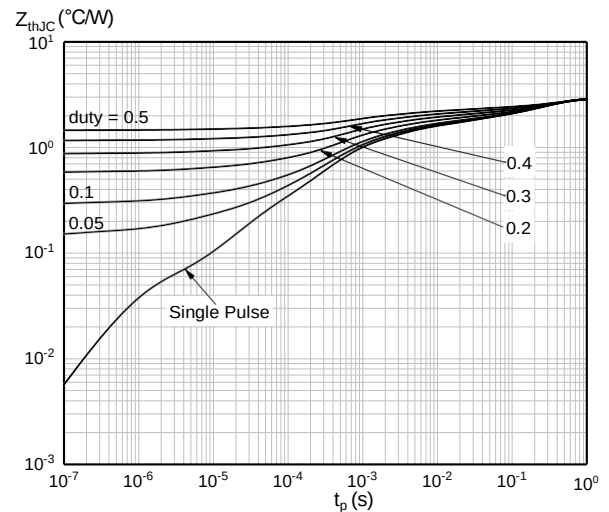


Figure 2. Maximum Transient Thermal Impedance

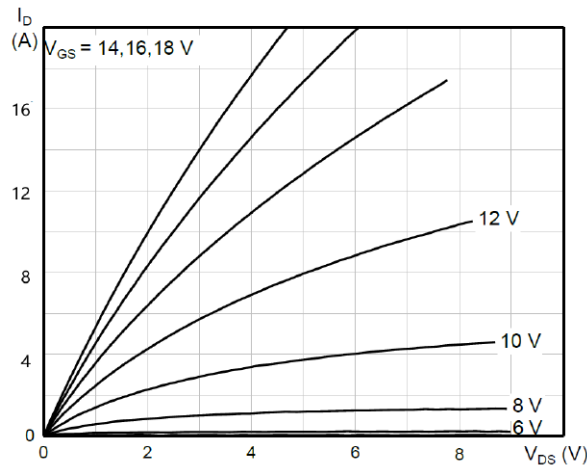


Figure 3. Typical Output Characteristics, $T_J = 25^\circ\text{C}$

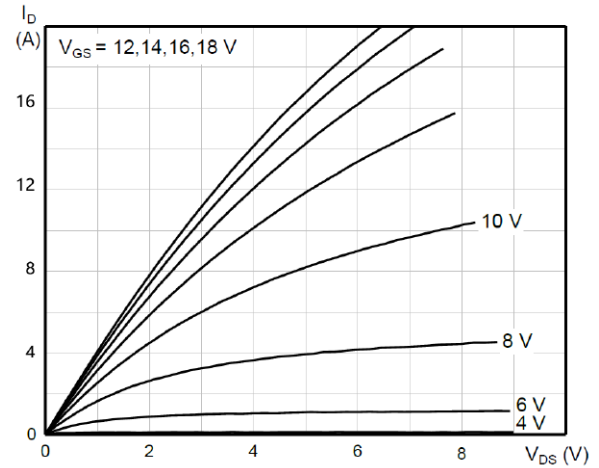


Figure 4. Typical Output Characteristics, $T_J = 175^\circ\text{C}$

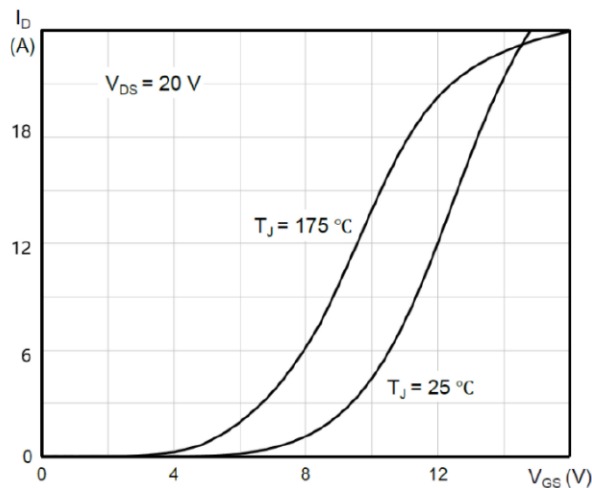


Figure 5. Typical Transfer Characteristics

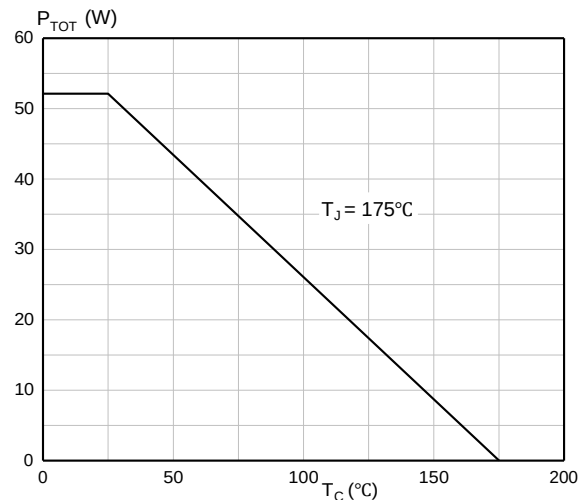


Figure 6. Total Power Dissipation

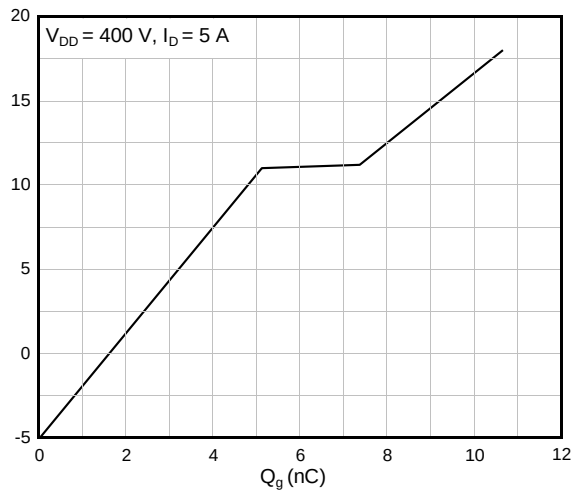


Figure 7. Typical Gate Charge Characteristics

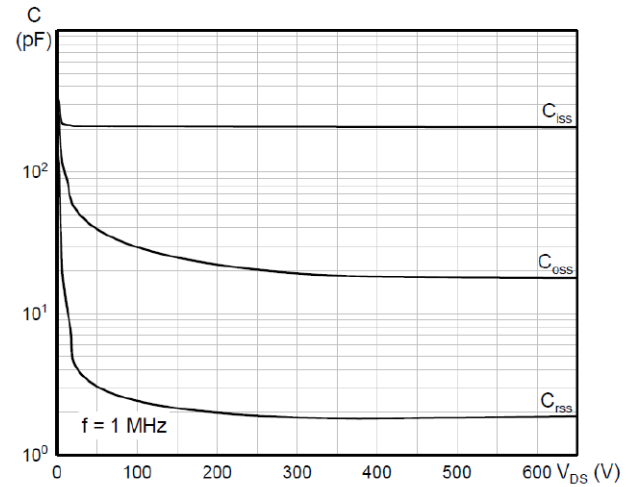


Figure 8. Typical Capacitance Characteristics

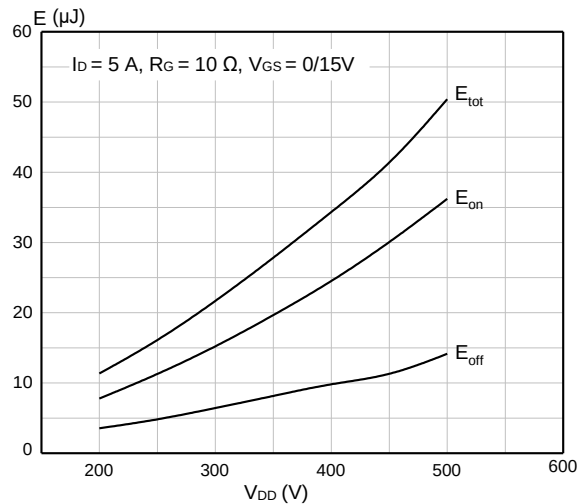


Figure 9. Typical Switching Energy vs. Supply Voltage

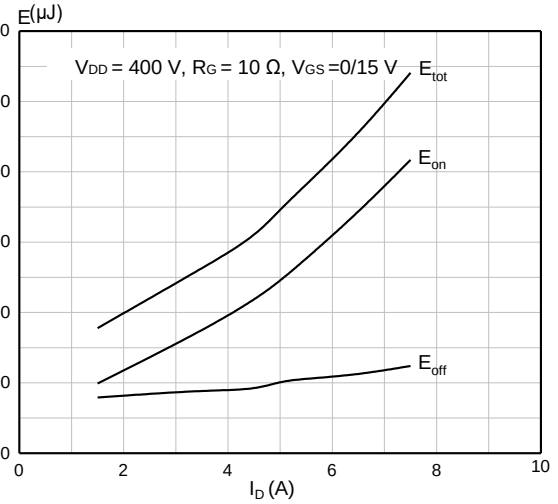


Figure 10. Typical Switching Energy vs. Drain Current

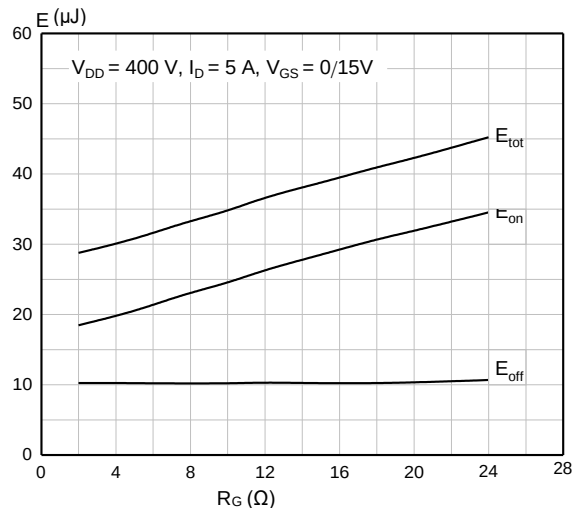


Figure 11. Switching Energy vs. Gate Resistance

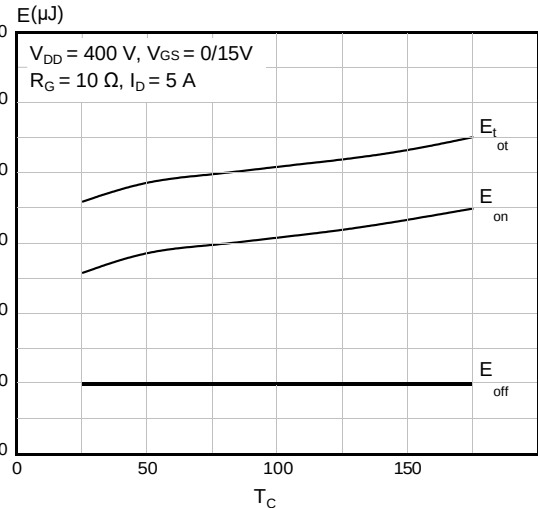


Figure 12. Typical Switching Energy vs. Temperature

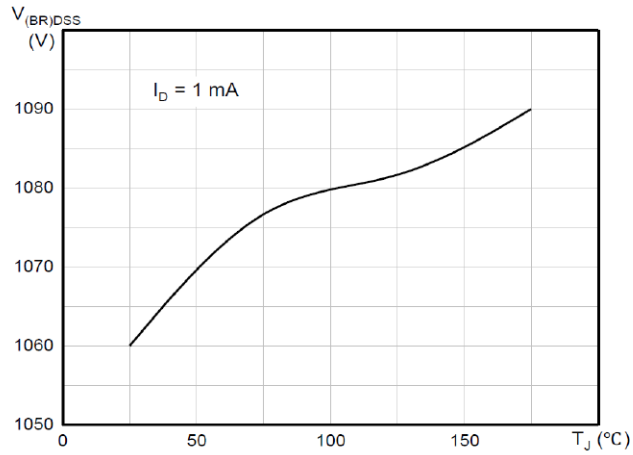


Figure 13. Breakdown Voltage vs. Temperature

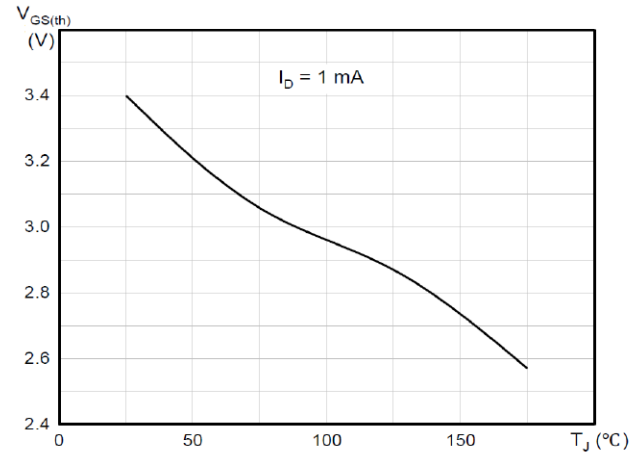


Figure 14. Gate Threshold vs. Temperature

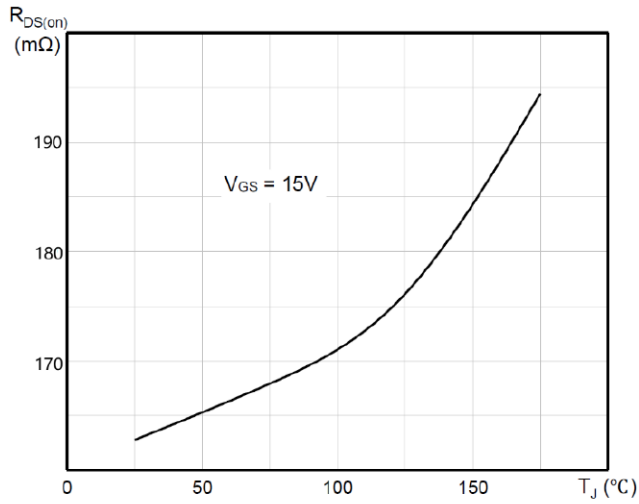


Figure 15. On-Resistance vs. Temperature

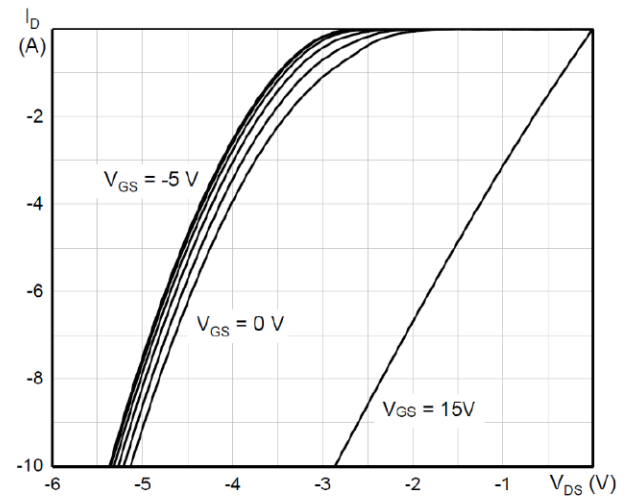
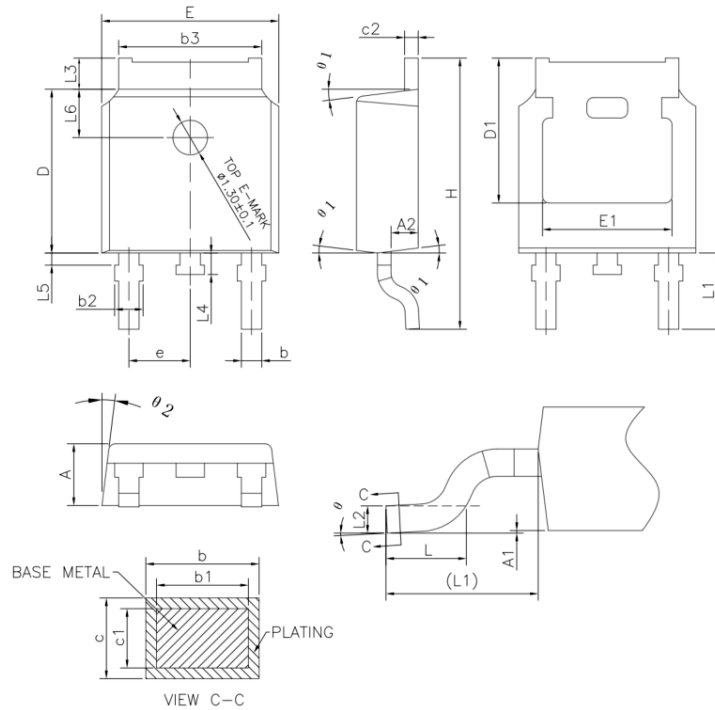


Figure 16. Body Diode Characteristics, T_J = 25°C



Package Dimensions

Package TO-252-2L



SYMBOL	Unit: mm		
	MIN	NOM	MAX
A	2.20	2.30	2.38
A1	0	-	0.10
A2	0.90	1.01	1.10
b	0.72	-	0.85
b1	0.71	0.76	0.81
b2	0.72	-	0.90
b3	5.13	5.33	5.46
c	0.47	-	0.60
c1	0.46	0.51	0.56
c2	0.47	-	0.60
D	6.00	6.10	6.20
D1	5.25	-	-
E	6.50	6.60	6.70
E1	4.70	-	-
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.508 BSC		
L3	0.90	-	1.25
L4	0.60	0.80	1.00
L5	0.15	-	0.75
L6	1.80 REF		
θ	0°	-	8°
θ1	5°	7°	9°
θ2	5°	7°	9°



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